5. (amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of claim 2, wherein there exists an oxidation induced stacking fault ring an inner diameter of which is 70% or less of an overall diameter, and in which there exists, surrounding the oxidation induced stacking fault ring, a defect free zone occupying 50% or more of a total surface area on one side.

B2 C

6. (amended) A silicon single crystal wafer, obtained from the silicon single crystal ingot of claim 2, wherein there exists an oxidation induced stacking fault ring an inner diameter of which is 50% or less of an overall diameter, and in which there exists, surrounding the oxidation induced stacking fault ring, a defect free zone occupying 75% or more of a total surface area on one side.

10. (amended) A silicon wafer for non-annealing, cut from a silicon ingot produced by the CZ method, wherein the silicon ingot is produced by pulling under a condition such that 1.15

B3 $< G1_{edge}/VG1_{center} \leq 1.25$ an inner diameter of an oxidation induced stacking fault ring is at least 1/2 a wafer inner diameter.

13. (amended) In a silicon wafer cut from a silicon ingot produced by the CZ method, a method to improve a gate oxide integrity in an area on the inside of an oxidation induced

B4 stacking fault ring by controlling a ratio of an oxidation induced stacking fault ring inner diameter to a crystal diameter, G1xG2, and $G1_{edge}/G1_{center}$.

Please add new claim 14.

14. The silicon wafer for non-annealing according to claim 10, wherein the silicon ingot has

B5 a density of void defects existing on the inside of an oxidation induced stacking fault ring reduced by expanding the inner diameter of the oxidation induced stacking fault.